SEMICONDUCTOR

10A GLASS PASSIVATED BRIDGE RECTIFIER

Data Sheet 1336 Rev.B

Features

- Glass Passivated Die Construction
- Low Reverse Leakage Current
- Low Power Loss, High Efficiency
- Electrically Isolated Epoxy Case for Maximum Heat Dissipation
- Case to Terminal Isolation Voltage 2500V
- UL Recognized File # E223064

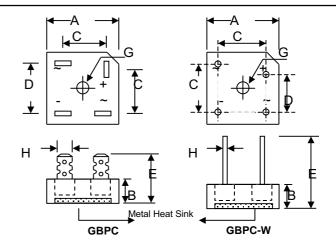
Mechanical Data

- Case: Epoxy Case with Heat Sink Internally Mounted in the Bridge Encapsulation
- Terminals: Plated Leads Solderable per MIL-STD-202. Method 208
- Polarity: Symbols Marked on Case
- Mounting: Through Hole for #8 Screw
- Weight: GBPC 24 grams (approx.)

GBPC-W 21 grams (approx.)

Marking: Type Number

"W" Suffix Designates Wire Leads
No Suffix Designates Faston Terminals
*All Models are Available on B(Height)=7.62mm Max. Epoxy Case



	GB	PC	GBPC-W						
Dim	Min	Max	Min	Max					
Α	28.40	28.70	28.40	28.70					
В	10.97	11.23	10.97	11.23					
С	15.70	16.70	17.10	19.10					
D	17.50	18.50	10.90	11.90					
E	22.86	25.40	30.50	_					
G	Hole for #8 screw, 4.90Ø Nominal								
Н	6.35 T	Typical	0.97Ø	1.07Ø					
All Dimension in mm									

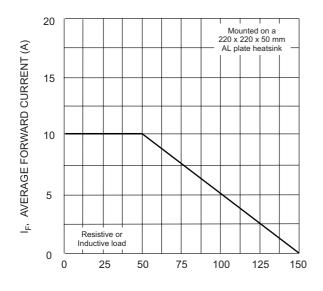
Maximum Ratings and Electrical Characteristics @TA=25°C unless otherwise specified

Single Phase, half wave, 60Hz, resistive or inductive load. For capacitive load, derate current by 20%.

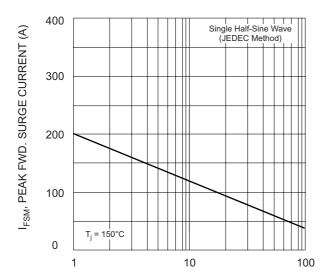
Characteristic	Symbol	GBPC 1000/W	GBPC 1001/W	GBPC 1002/W	GBPC 1004/W	GBPC 1006/W	GBPC 1008/W	GBPC 1010/W	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	Vrrm Vrwm Vr	50	100	200	400	600	800	1000	V
RMS Reverse Voltage	VR(RMS)	35	70	140	280	420	560	700	٧
Average Rectified Output Current @T _A = 50°C	lo	10						Α	
Non-Repetitive Peak Forward Surge Current 8.3ms Single half sine-wave superimposed on rated load (JEDEC Method)	IFSM	200							Α
Forward Voltage (per element) @I _F = 5.0A	Vғм	1.1						٧	
Peak Reverse Current @T _C = 25°C At Rated DC Blocking Voltage @T _C = 125°C	lгм	5.0 500						μA	
Typical Junction Capacitance (Note 1)	Cj	300							pF
Typical Thermal Resistance (Note 2)	R_{θ} JC	5.3							K/W
RMS Isolation Voltage from Case to Lead	Viso	2500						V	
Operating and Storage Temperature Range	Тj, Tsтg	-65 to +150						°C	

Note: 1. Measured at 1.0 MHz and applied reverse voltage of 4.0V D.C.

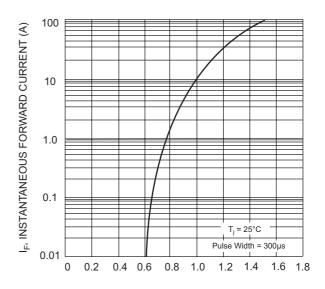
2. Thermal resistance junction to case per element mounted on heatsink.



 ${\rm T_A}, {\rm AMBIENT\ TEMPERATURE\ (^\circ C)}$ Fig. 1 Forward. Current Derating Curve



NUMBER OF CYCLES AT 60 Hz Fig. 3 Max Non-Repetitive Surge Current



 V_{F} , INSTANTANEOUS FORWARD VOLTAGE (V) Fig. 2 Typical Forward Characteristics (per element)

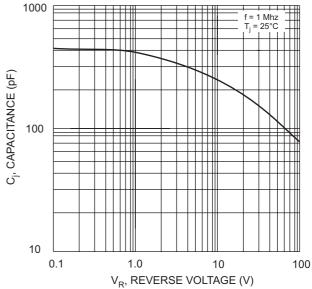
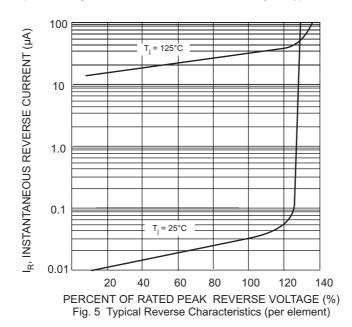


Fig. 4 Typical Junction Capacitance (per element)





TECHNICAL DATA

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